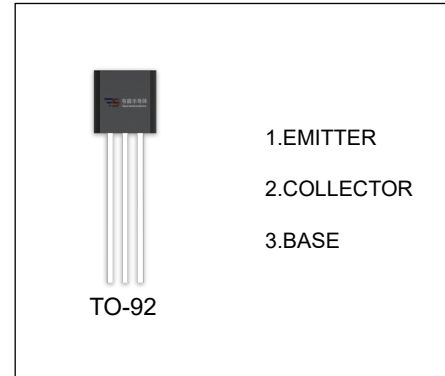


2SA1625 TRANSISTOR (PNP)

FEATURES

- High Voltage
- High Speed Switching
- Low Collector Saturation Voltage



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SA1625	TO-92	Bulk	1000pcs/Bag
2SA1625-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-400	V
V _{CEO}	Collector-Emitter Voltage	-400	V
V _{EBO}	Emitter-Base Voltage	-7	V
I _C	Collector Current -Continuous	-0.5	A
P _D	Collector Power Dissipation	750	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	166	°C /W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

T_a=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.1mA, I_C = 0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB} = -400V, I_E = 0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-10	μA
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -50mA$	40		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -10mA$			-1.2	V
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			20	pF
Transition frequency	f_T	$V_{CE} = -10V, I_C = -10mA$	20			MHz

CLASSIFICATION OF h_{FE}

RANK	M	L	K
RANGE	40-80	60-120	100-200

